

HAT2168H

Silicon N Channel Power MOS FET
Power Switching

REJ03G0046-0600Z

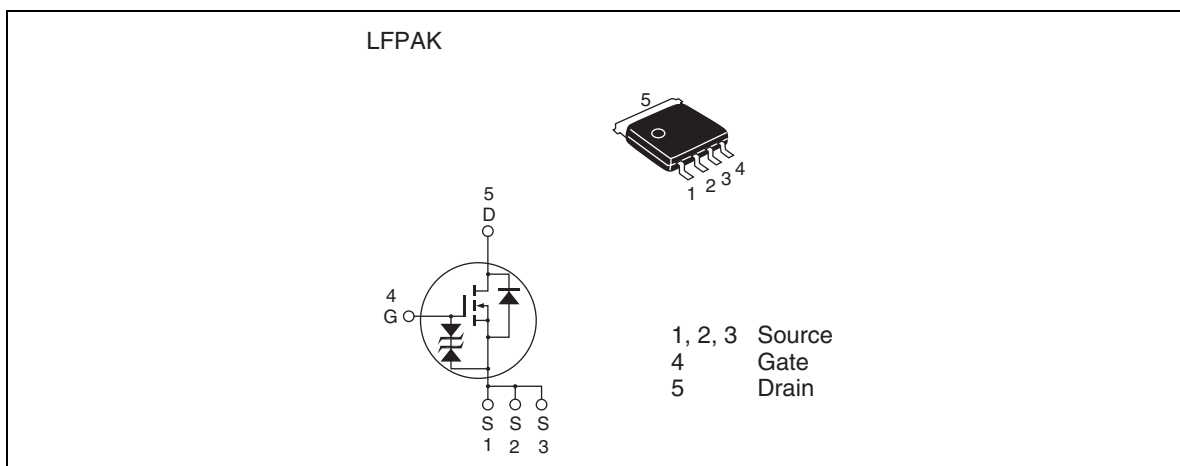
Rev.6.00

Jun.02.2003

Features

- High speed switching
 - Capable of 4.5 V gate drive
 - Low drive current
 - High density mounting
 - Low on-resistance
- $R_{DS(on)} = 6.0 \text{ m}\Omega$ typ. (at $V_{GS} = 10 \text{ V}$)

Outline



Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	30	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	30	A
Drain peak current	I _{D(pulse)} ^{Note1}	120	A
Body-drain diode reverse drain current	I _{DR}	30	A
Avalanche current	I _{AP} ^{Note 2}	15	A
Avalanche energy	E _{AR} ^{Note 2}	22	mJ
Channel dissipation	P _{ch} ^{Note3}	15	W
Channel to Case Thermal Resistance	θ _{ch-C}	8.33	°C/W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	– 55 to + 150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%
2. Value at T_{ch} = 25°C, R_g ≥ 50 Ω
3. T_c=25°C

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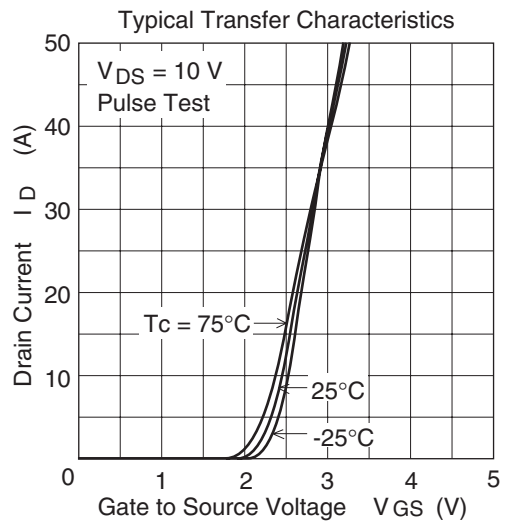
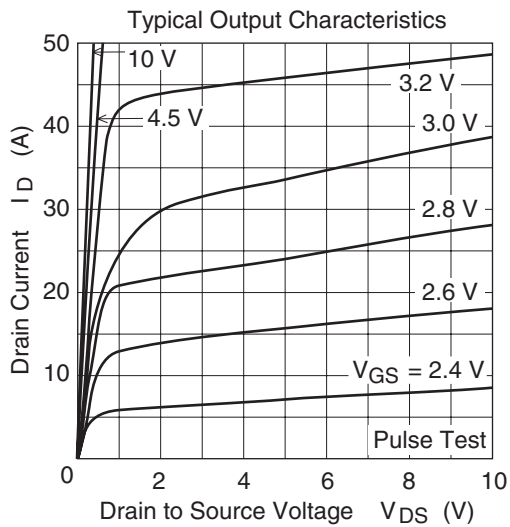
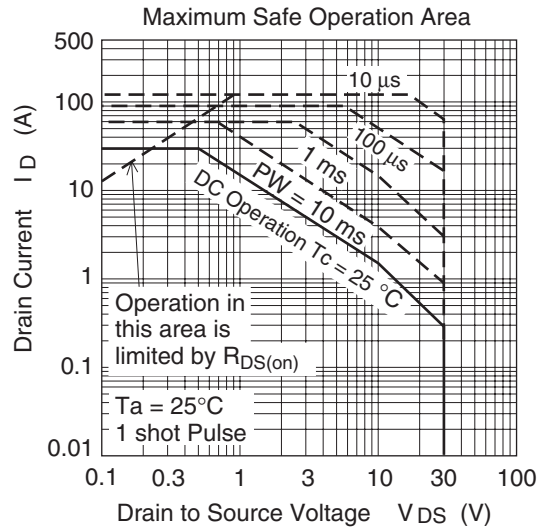
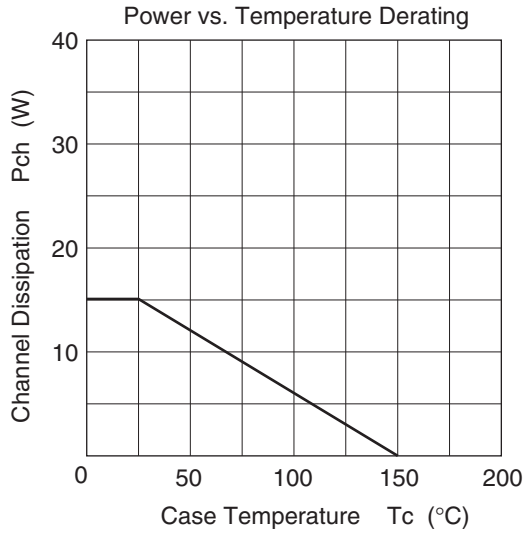
Electrical Characteristics

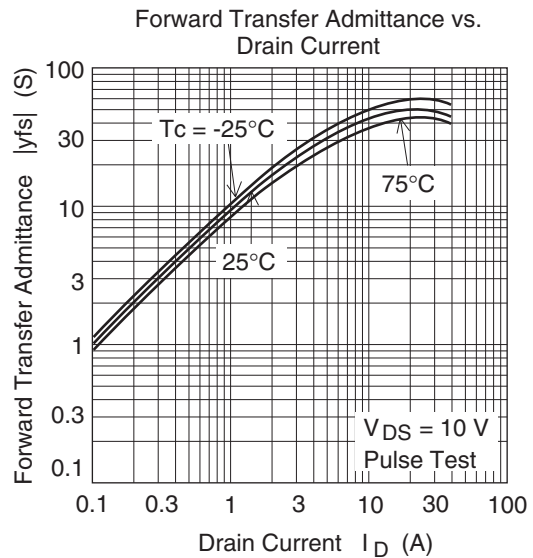
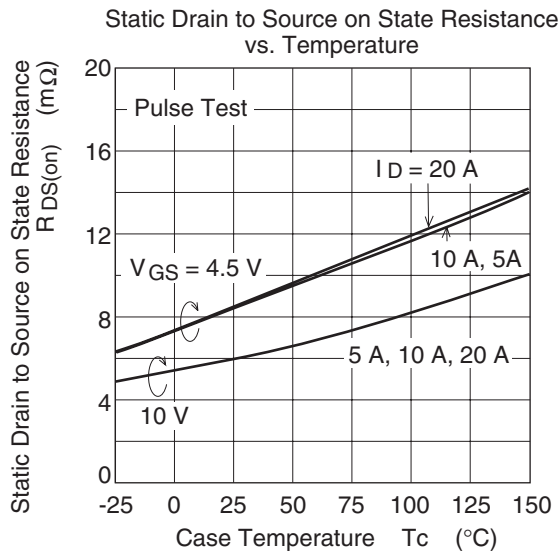
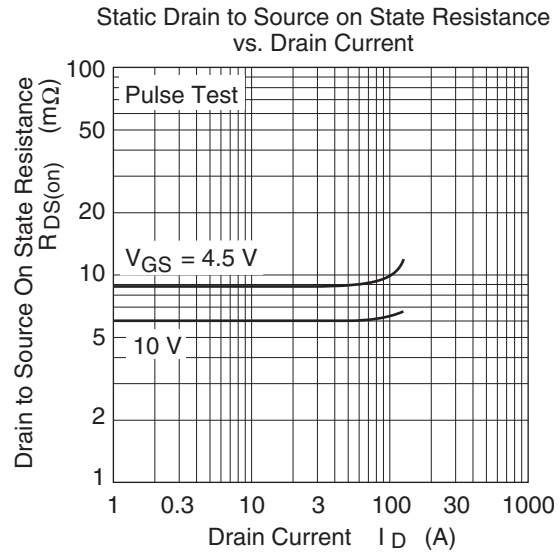
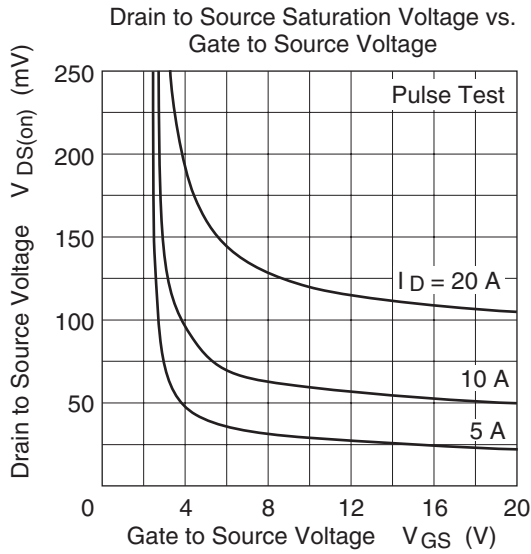
(Ta = 25°C)

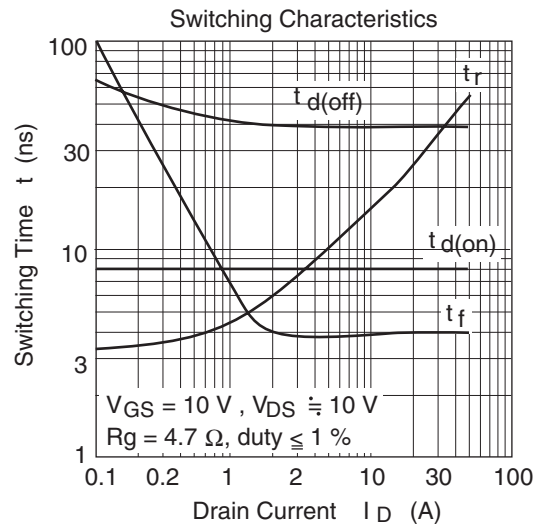
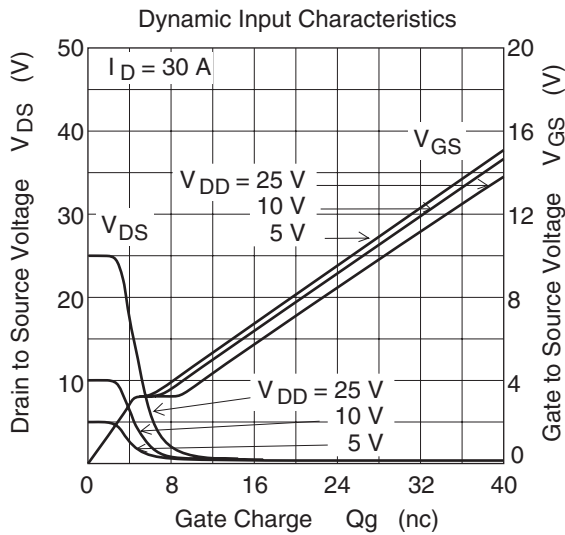
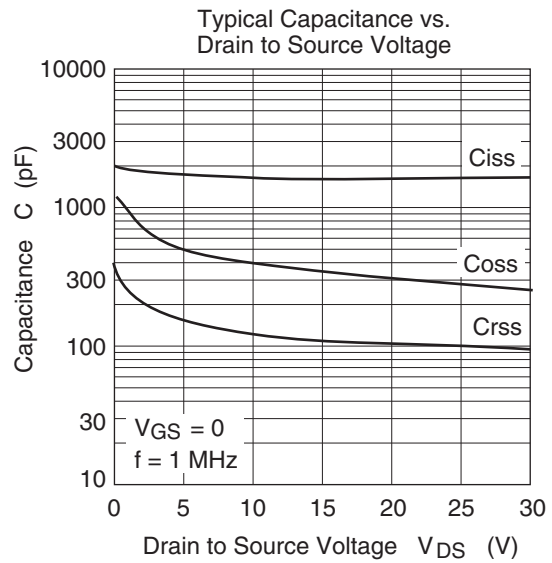
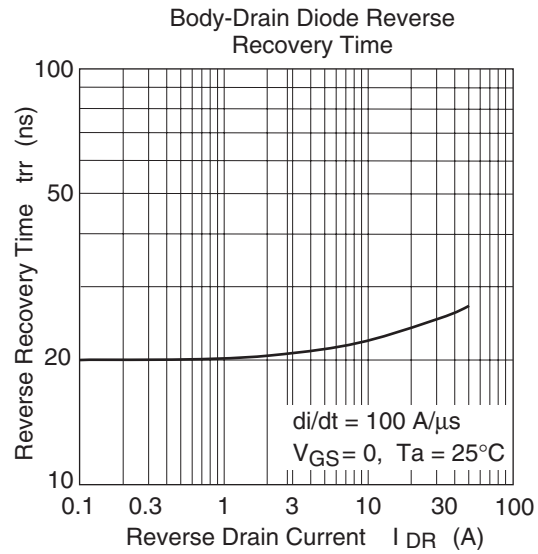
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 20	—	—	V	$I_G = \pm 100 \text{ }\mu\text{A}$, $V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 16 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	1	μA	$V_{DS} = 30 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.5	V	$V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$
Static drain to source on state resistance	$R_{DS(on)}$	—	6.0	7.9	$\text{m}\Omega$	$I_D = 15 \text{ A}$, $V_{GS} = 10 \text{ V}$ ^{Note4}
	$R_{DS(on)}$	—	8.8	13.5	$\text{m}\Omega$	$I_D = 15 \text{ A}$, $V_{GS} = 4.5 \text{ V}$ ^{Note4}
Forward transfer admittance	$ y_{fs} $	30	50	—	S	$I_D = 15 \text{ A}$, $V_{DS} = 10 \text{ V}$ ^{Note4}
Input capacitance	C_{iss}	—	1730	—	pF	$V_{DS} = 10 \text{ V}$
Output capacitance	C_{oss}	—	400	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	130	—	pF	$f = 1 \text{ MHz}$
Gate Resistance	R_g	—	0.55	—	Ω	
Total gate charge	Q_g	—	11	—	nc	$V_{DD} = 10 \text{ V}$
Gate to source charge	Q_{gs}	—	5	—	nc	$V_{GS} = 4.5 \text{ V}$
Gate to drain charge	Q_{gd}	—	2.4	—	nc	$I_D = 30 \text{ A}$
Turn-on delay time	$t_{d(on)}$	—	8	—	ns	$V_{GS} = 10 \text{ V}$, $I_D = 15 \text{ A}$
Rise time	t_r	—	20	—	ns	$V_{DD} \approx 10 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	40	—	ns	$R_L = 0.67 \text{ }\Omega$
Fall time	t_f	—	4	—	ns	$R_g = 4.7 \text{ }\Omega$
Body-drain diode forward voltage	V_{DF}	—	0.85	1.10	V	$I_F = 30 \text{ A}$, $V_{GS} = 0$ ^{Note4}
Body-drain diode reverse recovery time	t_{rr}	—	25	—	ns	$I_F = 30 \text{ A}$, $V_{GS} = 0$ $diF/dt = 100 \text{ A}/\mu\text{s}$

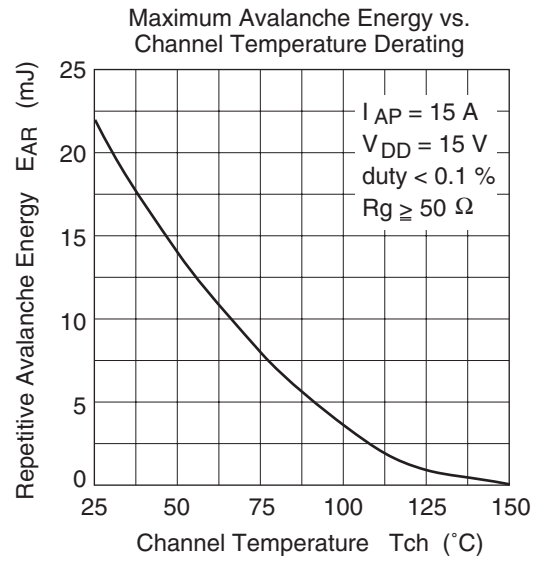
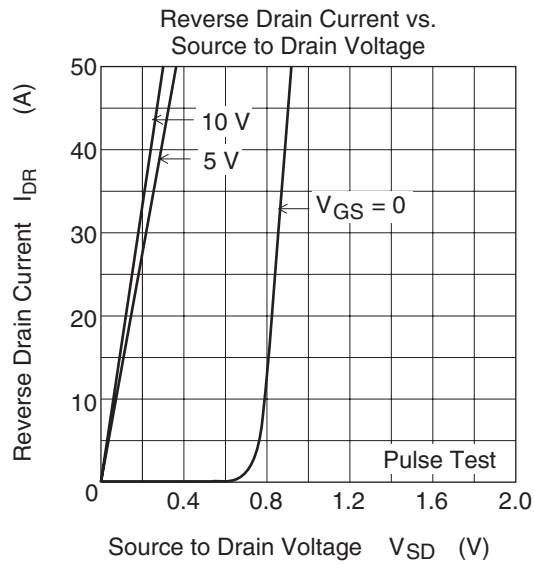
Notes: 4. Pulse test

Main Characteristics

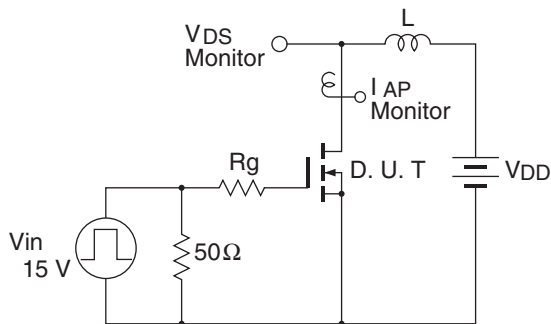






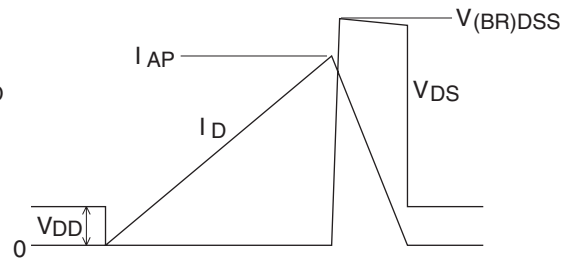


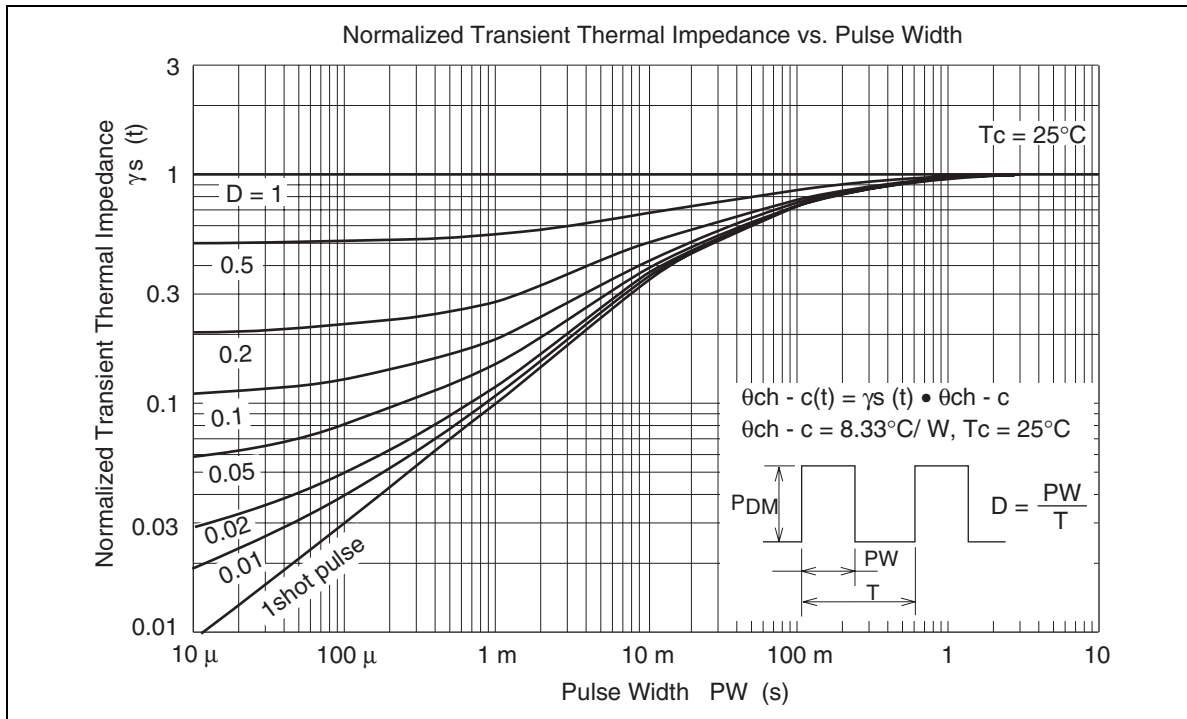
Avalanche Test Circuit



Avalanche Waveform

$$E_{AR} = \frac{1}{2} L \cdot I_{AP}^2 \cdot \frac{V_{DSS}}{V_{DSS} - V_{DD}}$$

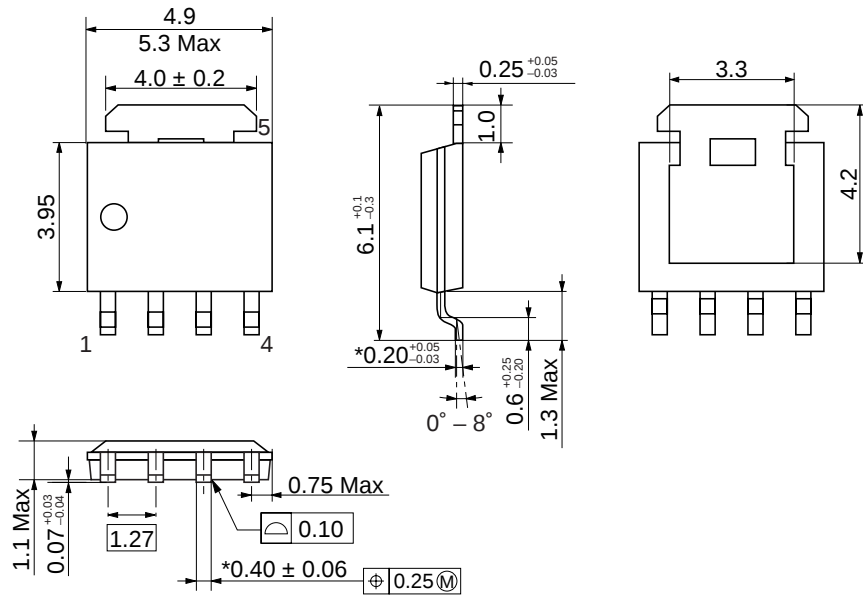
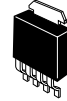




Package Dimensions

As of January, 2003

Unit: mm



*Ni/Pd/Au plating

Package Code	LFPAK
JEDEC	—
JEITA	—
Mass (reference value)	0.080 g

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